



**liten**  
cea tech



## CELL SESSION INTRODUCTION

*BIFIPV workshop –Miyazaki 29-30/09/2016*  
*Y. Veschetti*



## OUTLINE

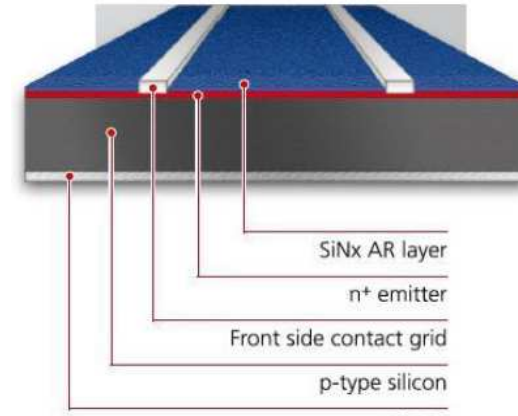
- **CURRENT TRENDS IN PV CELLS TECHNOLOGY**
- **STATUS OF BIFACIAL CELL TECHNOLOGIES**
  - Well known players: status & improvement
  - A new « challenger »
  - Alternatives approaches
- **CONCLUSION & PERSPECTIVES**



# AL-BSF TECHNOLOGY

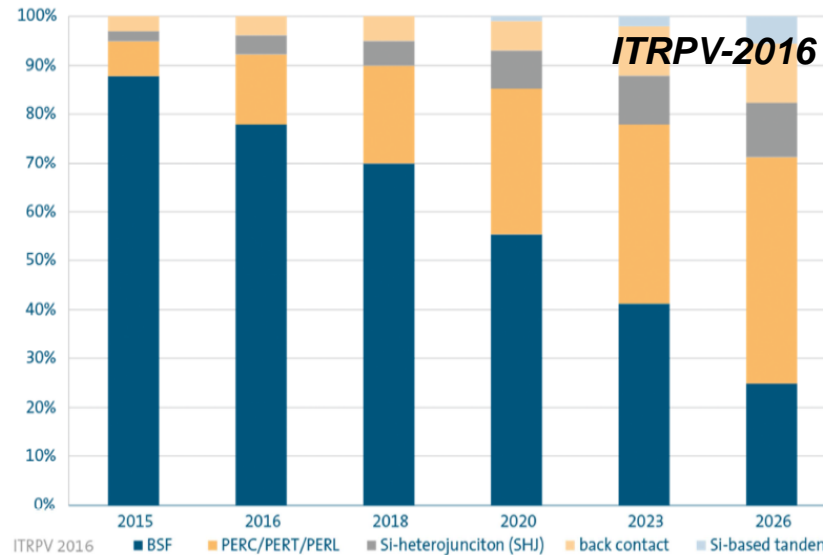
- 75% of market share in 2016
- Very simple process
- Compatible with p-type mc-Si and mono-Si
- Continuous efficiency improvement
  - 16% - 17% in 2006 on Cz
  - 19% - 20% in 2016

## AI-BSF Standard Cell



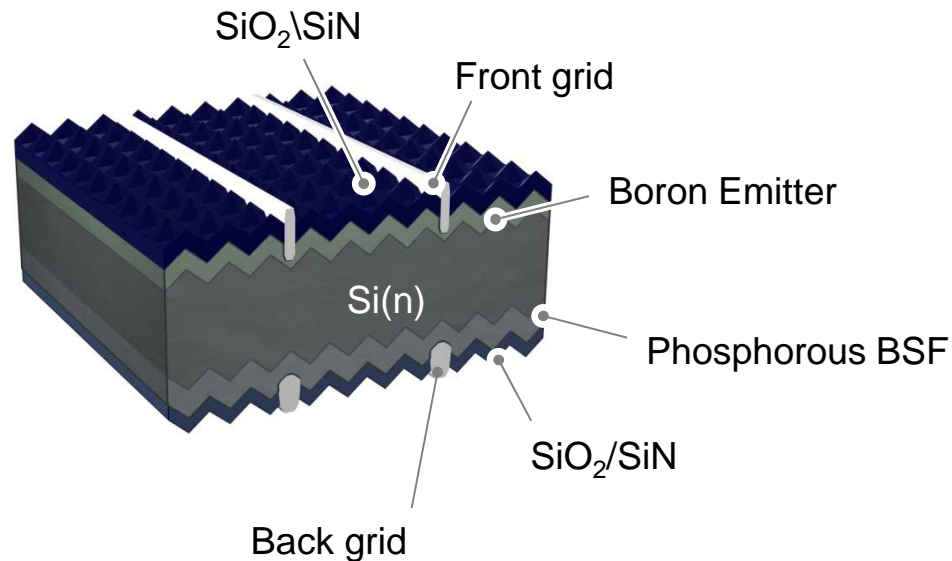
Rear reflectance: 60%  
Rear recombination velocity: 160cm/s

- Al-BSF cell shows now efficiency limitation
- Producers consider alternatives
- Most of the alternatives can be bifacial



## PERT CELL

**PERT**: Passivated Emitter Rear Totally diffused



### **Mean features:**

- ✓ Mostly developed on n-type Cz Si
- ✓ Naturally bifacial if metallization are screen-printed
- ✓ High bifaciality: > 90%
- ✓ Good compatibility with existing production lines

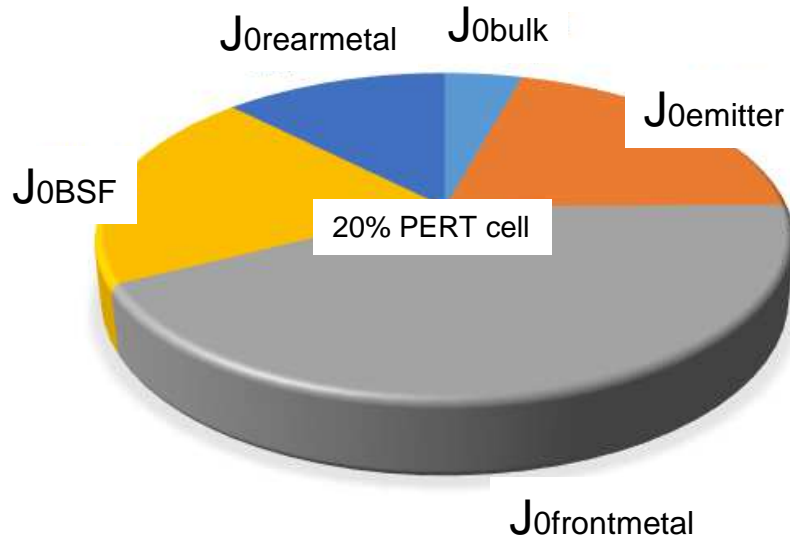
### **Efficiency records:**

- From 18.5% in 2009
- 20.7% in 2014
- **21.5% in 2016**

- R&D actors: ISFH, ISC, ECN, CEA, MOTECH, IMEC, SUNIVA, Univ Konstanz, ISE, ...
- Producers: PVGS, NSP, MEGACELL, LG, YINGLI, SNEED, ...
- Estimated world production capacity ~ 1GW up to 1.5 GW



# PERT CELL: EFFICIENCY ISSUE



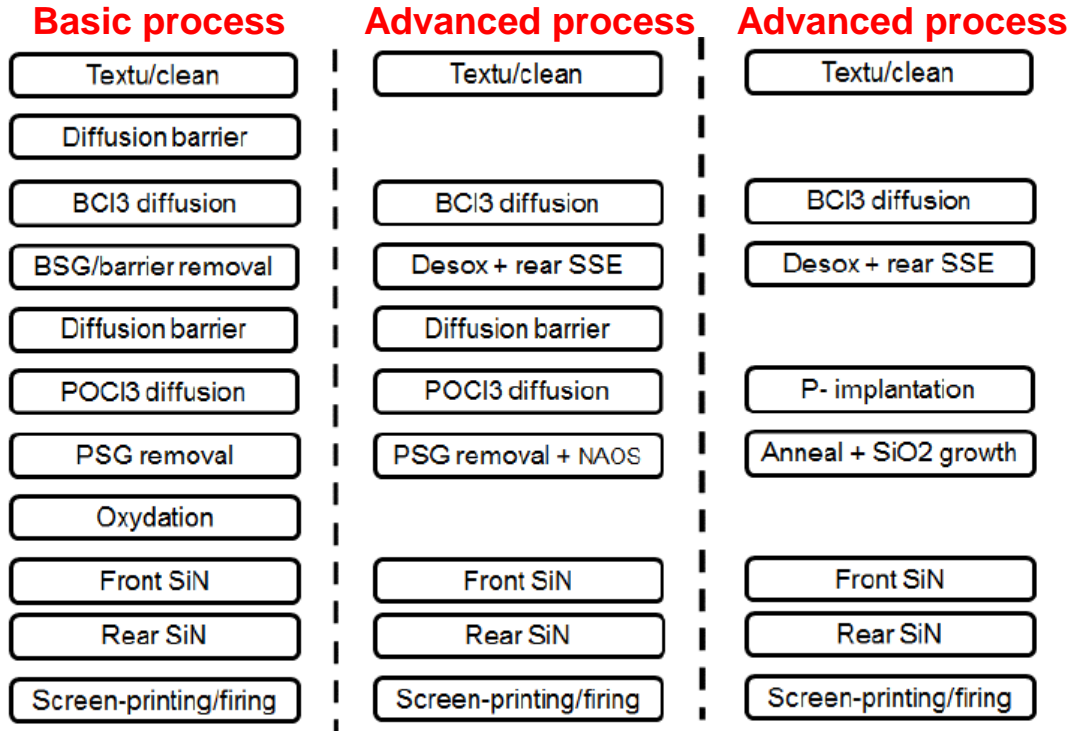
- Recombination at the metal/B-emitter interface has been the main efficiency issue ( $J_{0met}$ : 2000-5000 fA/cm<sup>2</sup>)
- Solutions investigated:
  - Modification of emitter profile (Selective Em)
  - Limitation of contacting pastes area
  - New pastes generation

	Voc (mV)	Jsc (mA/cm <sup>2</sup> )	FF (%)	Efficiency (%)	Area (cm <sup>2</sup> )	Specificities
Average current performance	660	39.5	79.0	20.5	239	
LG	≈ 680	≈ 39.3	xxx	21-22	239	Screen-printing
ECN/TEMPRESS	675	38.8	79.1	20.7	239	Screen-printing + back N+ poly-Si
REC				21.5		See presentation BIFI2016
ISFH				~21.5		F. Kiefer, published in Solmat
IMEC	689	40.3	80.9	22.5	239	Cu plating – not bifacial
TRINA	684	41.0	81.2	22.8	149	Cu plating – not bifacial



# PERT: SIMPLIFICATION PROCESSES

- PERT process flow potentially quite complexe (= costly)
- Gas diffusion: BBr3 mostly used in industry for n-PERT cells
- Simplification processes have been developed (ISC BiSoN, ECN n-PASHA)
- ➔ Using the texturing step to etch-off the doped region
- ➔ Conserving the BSG from diffusion as a passivation layer
- ➔ Combination with P-implantation



# PERT: SIMPLIFICATION PROCESSES

- Solid sources approach: spin-on, PECVD, APCVD
- ➔ Process complexity also reduced for a similar potential in efficiency

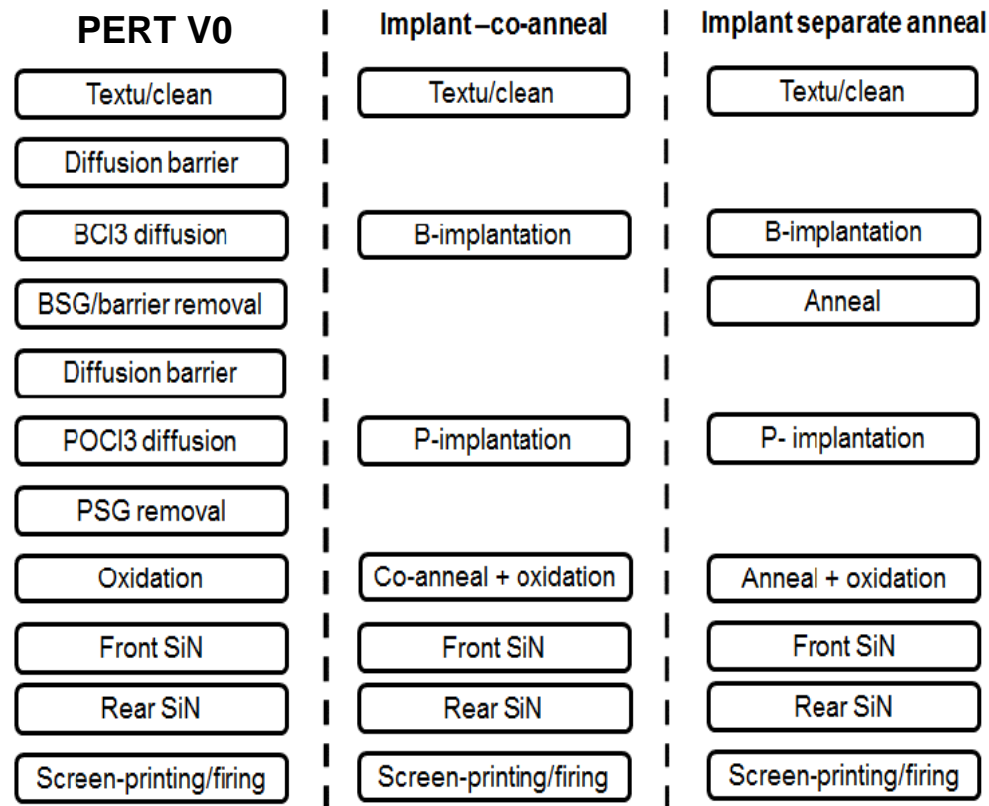
**Example: ultrasimplified process using multifonctional layers with Solenna 3 concept (CEA-INES)**

<b>SOLENN</b>	<b>SOLENNA 1</b>	<b>SOLENNA 2</b>	<b>SOLENNA3</b>
Gas diffusion	Mixed co-diffusion	Mixed co-diffusion	Multifunctional layers
Texturing/cleaning	Texturing/cleaning	Texturing/cleaning	Texturing/cleaning
Back diffusion barrier			
Boron diffusion	SiO <sub>x</sub> :B	SiO <sub>x</sub> :B	SiO <sub>x</sub> :B
Barrier & BSG removal		SiO <sub>x</sub> :P	SiN <sub>x</sub> :P
Front diffusion barrier			
POCl <sub>3</sub> diffusion	POCl <sub>3</sub> co-diffusion	Annealing	Annealing
Barrier & PSG removal	SiO <sub>x</sub> :B & PSG removal	SiO <sub>x</sub> :B & SiO <sub>x</sub> :P removal	
Thermal oxidation	Thermal oxidation	Thermal oxidation	
Front & rear SiN <sub>x</sub>	Front & rear SiN <sub>x</sub>	Front & rear SiN <sub>x</sub>	Front SiN <sub>x</sub>
Screen-printing	Screen-printing	Screen-printing	Screen-printing
Firing	Firing	Firing	Firing
<b>12 steps</b>	<b>9 steps</b>	<b>10 steps</b>	<b>7 steps</b>



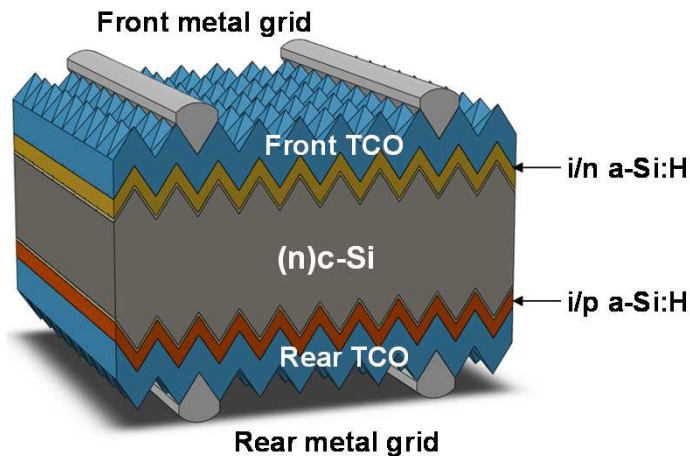
# PERT: SIMPLIFICATION PROCESSES

- Implantation approach:
- ➔ High efficiency (> 20.5%) obtained in 2014/15 (ISFH, Bosch) but BL approach too costly (CAPEX)
- ➔ Alternatives under development: Ion Shower (Intevac, Ulvac), plasma immersion (IBS)





## A-SI:H/C-SI HETEROJUNCTION SOLAR CELLS (HJT)



### Key features:

- ✓ Mostly developed on n-type Cz Si
- ✓ Naturally bifacial if metallization are screen-printed
- ✓ High bifaciality: > 90%
- ✓ Simple process
- ✓ No compatible with existing production lines
- ✓ Excellent T coeff (-0,25%/°C)

### Efficiency records:

- 24.7% (Sanyo-Panasonic)
- Production efficiency: 21%-22%

- R&D actors: CEA-INES, CSEM, KANEKA, CHOSCHU,
- Industrial actors: SANYO-PANASONIC, SILEVO, SUNPREME, ECOSOLIFIER, AUO, MEYER-BURGER
- Estimated world production capacity ~ 1200MW

## EFFICIENCY RECORD FOR HJT BIFACIAL CELLS

Institut/ Industrial	Efficiency (%)	area (cm <sup>2</sup> )	Description	Bifacial	Pays
Panasonic	24.7	100 Thickness 100μm	Ag screen-printing, low damage TCO	✓	JP
Choshu	24.1	239 GT, BB less	Ag screen-printing, low damage TCO	✓	JP
AUO	23.1	240	Ag screen-printing, low damage TCO	✓	TW
SILEVO	23.1	240	Cu plating, low damage TCO	✓	USA
R&R MB	23.3	240 GT, BB less	Ag screen-printing	✓	CH
CSEM	22.8	239 GT, BB less	Ag screen-printing	✓	CH

- Many existing pilot-lines ~ Meyer Burger, INES, ENN solar, ...
- Improvements on alternatives to high metalized fraction → Smartwire (SWCT), > 5 busbars

### Remaining challenges:

- Efficiency: Optical losses & lateral carrier transport: a-Si:H, TCO
- High bulk lifetime required: cost of n-type premium wafer
- CAPEX of production line

## ALTERNATIVES APPROACHES

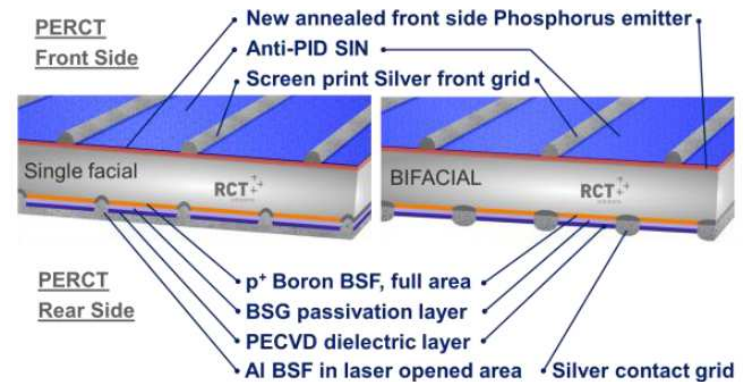
- Currently, cost of n-type wafer higher than p-type (10% up to 20%)
- ➔ Very strong limitation for competitiveness of n-PERT or HJT

- **Existing alternatives:**

### 1. PERCT technology (RCT)

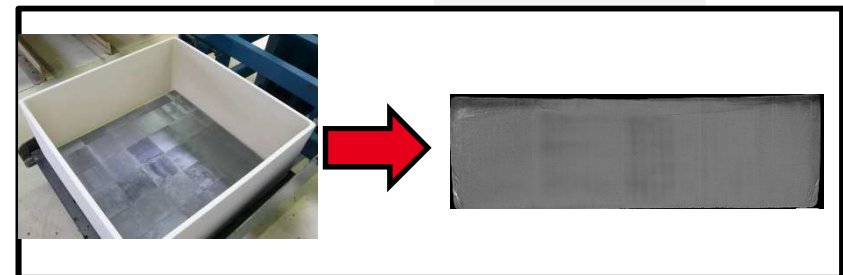
➔ mc-BIFACIAL cells got average 18.56% with 87% bifaciality on pilot line

*Andreas Tepe et al. 31st European Photovoltaic Solar Energy Conference and Exhibition*



### 2. N-PERT on monolike silicon (CEA-INES & ECM GreenTech)

- ➔ Average efficiency = 19% on entire brick of G5 ingot
- ➔ Adapted process to limit dispersion (dislocation impact)

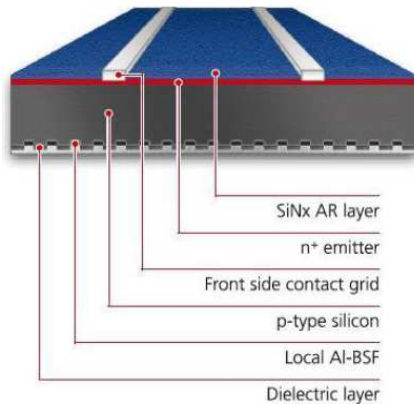


*R.Cabal et al. 20% PERT technology adapted to n-type monolike silicon, 29th European Photovoltaic Solar Energy Conference and Exhibition*

## PERC+: A NEW CHALLENGER

### PERC Technology

High-efficiency p-type solar cells



**Rear reflectance: 90%**

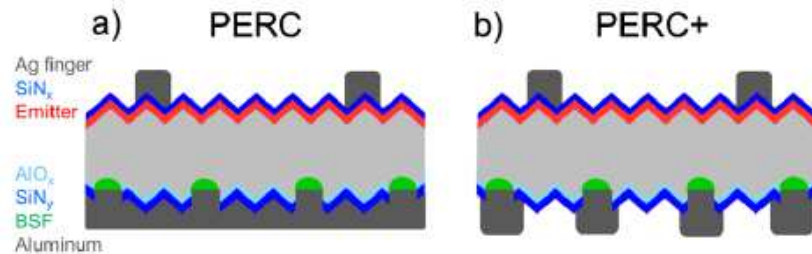
**Rear recombination velocity: 60cm/s**

### Key features of PERC cell:

- Mass production:  $\eta > 20.5\%$
- Record lab:  $\eta = 22.1\%$
- p-type Cz
- 3 additional steps
- LID is not an issue anymore

*PV-Tech.org (05/07/2016)*

*Trina Solar pushes average P-type mono PERC cell efficiencies to 21.1%*

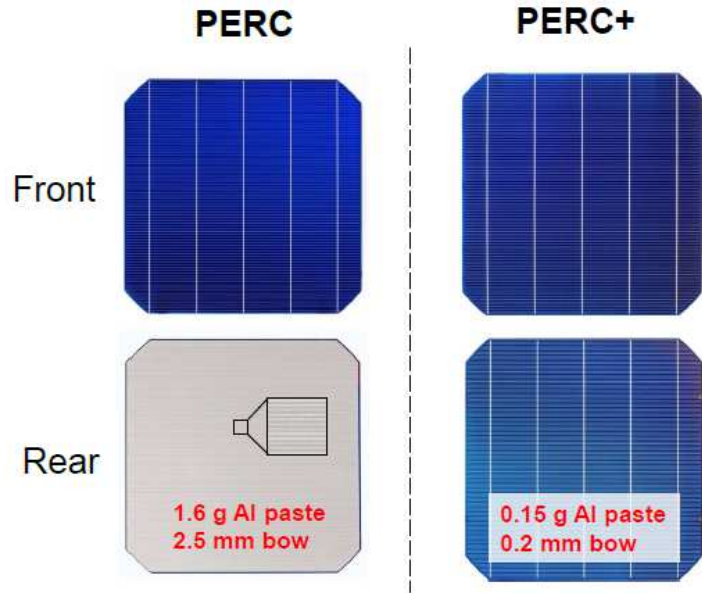


- Conversion from PERC to PERC+
- In 2015:  $\eta = 21\%$  on large area
- In production @ Solarworld

**Thorsten Dullweber et al. PERC+: industrial PERC solar cells with rear Al grid enabling bifaciality and reduced Al paste consumption, Prog. Photovolt: Res. Appl. (2015)**



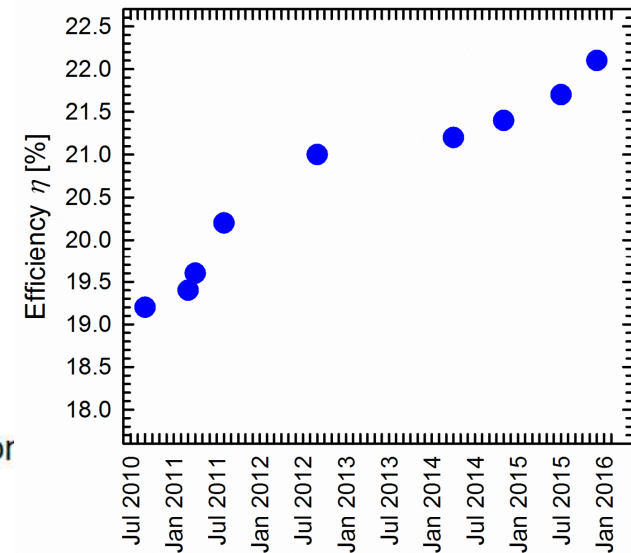
# BIFACIAL PERC = PERC +



PERC+ @ ISFH

- $\eta_{\text{front}} = 21.5\%$
- $\eta_{\text{rear}} = 16.7\%$
- Bifaciality 80%

PERC+ in pilot production @ SolarWorld



- Improvement in PERC+ efficiency: 21.5%
- Expect 23% efficiency in 2 years
- More and more Al-BSF fabs are upgraded to p-PERC.

Thorsten Dullweber, NREL Workshop 2016



- **Larger choice in bifacial cell technologies**
  - **Since 2014, regular improvements on PERT and HJT cells**
  - **2015: PERC+ is one more serious competitor**
  - **Alternatives: p-PERT, PERCT, n-PERT ML, Bifacial IBC**
  
- **Development of bifacial will be related to the race for higher efficiency and cost reduction.**
- **Bifaciality factor/rear efficiency is probably not the main driver**
- **Optimization for bifaciality can justified the path to > 5 busbars/half cells**
  
- **Perspectives:**
  - ➔ **In a short term and for efficiency < 22%, PERC is relevant**
  - ➔ **PERT could compete but cost n-type wafer and efficiency limitation are issues**
  - ➔ **For  $\eta > 23\%$ , heterojunction could be the best candidate**
  - **Improvements in high quality wafers and production cost will be strong influents factors.**



**MERCI POUR VOTRE ATTENTION**

**THANKS FOR YOUR ATTENTION**

---

Commissariat à l'énergie atomique et aux énergies alternatives  
Alternative Energies and Atomic Energy Commission  
17 av des martyrs 38000 GRENOBLE France  
<http://liten.cea.fr>

Établissement public à caractère industriel et commercial  
Public establishment with commercial and industrial character  
RCS Paris B 775 685 019

INES Site  
Institut National de l'Energie Solaire  
National Solar Energy Institute  
50 avenue du lac Léman  
73375 Le Bourget-du-Lac France  
+33 4 79 79 20 00